

Dual N-Channel 30-V (D-S) MOSFET

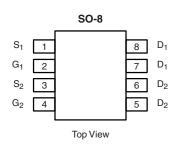
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
30	0.035 at V _{GS} = 10 V	6.0		
	0.052 at V _{GS} = 4.5 V	4.9		

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Compliant to RoHS Directive 2002/95/EC

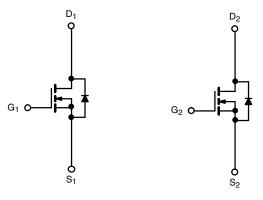






Ordering Information: Si9936BDY-T1-E3 (Lead (Pb)-free)

Si9936BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current /T 150 °C\a	T _A = 25 °C	I _D	6.0	4.5	Δ.
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		4.8	3.6	
Pulsed Drain Current		I _{DM}	40		Α
Continuous Source Current (Diode Conduction) ^a		I _S	1.7	0.9	
W	T _A = 25 °C	- P _D	2.0	1.1	W
Maximum Power Dissipation ^a	T _A = 70 °C		1.3	0.7	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manipular to Australia	t ≤ 10 s	- R _{thJA}	53	62.5	°C/W
Maximum Junction-to-Ambient ^a	Steady State		92	110	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	30	40	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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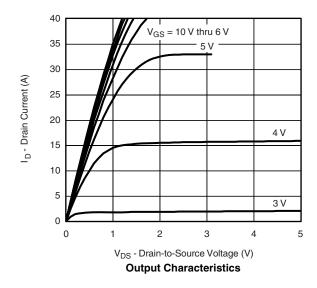
Parameter	Symbol	Test Conditions		Тур.	Max.	Unit
Static	•					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$ 1.0		3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zana Cata Valtana Busin Comunit	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μΑ
Zero Gate Voltage Drain Current		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α
Drain-Source On-State Resistance ^a	D	$V_{GS} = 10 \text{ V}, I_D = 6 \text{ A}$		0.028	0.035	0
	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 4.9 A		0.041	0.052	Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 6 A		12		S
Diode Forward Voltage ^a	V_{SD}	I _S = 1.7 A, V _{GS} = 0 V		0.8	1.2	٧
Dynamic ^b				•		
Total Gate Charge	Q_g			8.6	13	
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 6 \text{ A}$		1.8		nC
Gate-Drain Charge	Q _{gd}			1.5		
Gate Resistance	R_g	f = 1 MHz		2.8		Ω
Turn-On Delay Time	t _{d(on)}			10	15	
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		15	25	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 1 \text{ A, V}_{GEN} = 10 \text{ V, R}_g = 6 \Omega$		25	40	ns
Fall Time	t _f			10	15	
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 1.7 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$		20	40	

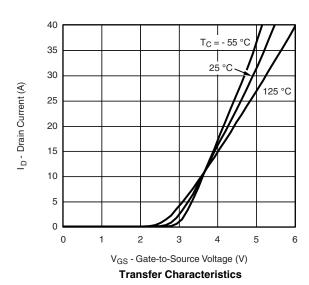
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

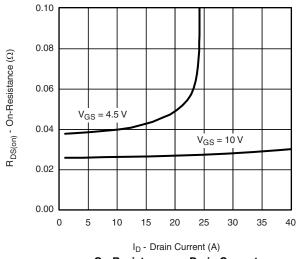




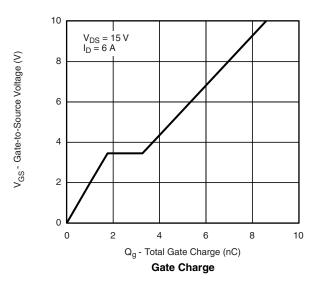




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On-Resistance vs. Drain Current



10 T_J = 150 °C

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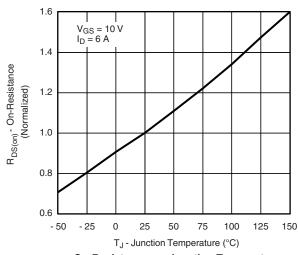
10 T_J = 25 °C

10 V_{SD} - Source-to-Drain Voltage (V)

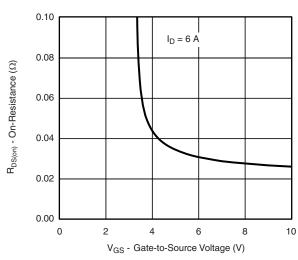
Source-Drain Diode Forward Voltage

800 700 600 C_{iss} C - Capacitance (pF) 500 400 300 200 100 0 0 5 10 15 20 25 30

V_{DS} - Drain-to-Source Voltage (V) **Capacitance**



On-Resistance vs. Junction Temperature



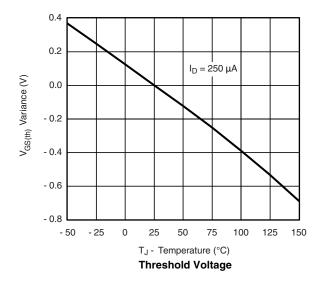
On-Resistance vs. Gate-to-Source Voltage

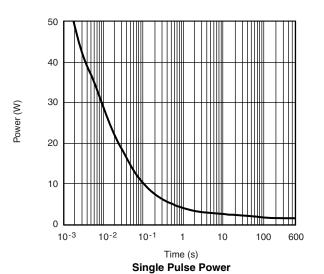
Is - Source Current (A)

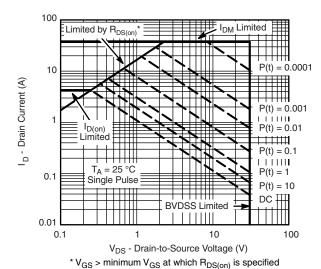
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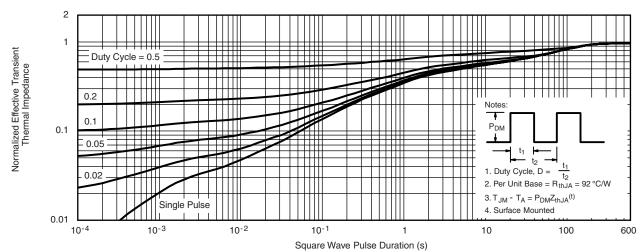
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







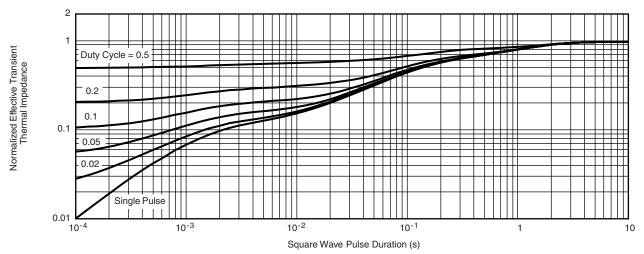




Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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